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FDS6572A

20V N-Channel PowerTrench® MOSFET

General Description

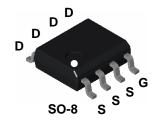
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low R_{DS(ON)} and fast switching speed.

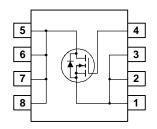
Applications

DC/DC converter

Features

- 16 A, 20 V. $R_{DS(ON)} = 6 \ m\Omega \ @ \ V_{GS} = 4.5 \ V$ $R_{DS(ON)} = 8 \ m\Omega \ @ \ V_{GS} = 2.5 \ V$
- Low gate charge (57 nC)
- High performance trench technology for extremely low $R_{\text{DS(ON)}}$
- · High power and current handling capability





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		20	V
V _{GSS}	Gate-Source Voltage		±12	V
I _D	Drain Current - Continuous	(Note 1a)	16	А
	– Pulsed		80	
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1.0	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +175	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
R _{e,IC}	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6572A	FDS6572A	13"	12mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$	20			V
$\Delta BV_{DSS} \over \Delta T_{.1}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		12		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			1	μΑ
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -12 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_{D} = 250 \mu A$	0.6	8.0	1.5	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		-4		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$ $V_{GS} = 2.5 \text{ V}, I_D = 14 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}, T_J = 125 ^{\circ}\text{C}$		4 5 5.7	6 8 9	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	40			Α
g _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, \qquad I_{D} = 16 \text{ A}$		96		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		5914		pF
Coss	Output Capacitance	f = 1.0 MHz		1433		pF
C _{rss}	Reverse Transfer Capacitance			797		pF
Switchir	ng Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, \qquad I_D = 1 \text{ A},$		21	34	ns
t _r	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		25	40	ns
t _{d(off)}	Turn-Off Delay Time	7		102	163	ns
t _f	Turn-Off Fall Time			66	106	ns
Q _g	Total Gate Charge	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 16 \text{ A},$		57	80	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 4.5 V		10		nC
Q_{gd}	Gate-Drain Charge			16		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain–Source	•			2.1	Α
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.1 A (Note 2)		0.6	1.2	V

Notes:

^{1.} R_{8JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{8JC} is guaranteed by design while R_{8CA} is determined by the user's board design.



a) 50°C/W when mounted on a 1in² pad of 2 oz copper



b) 105°C/W when mounted on a .04 in² pad of 2 oz copper



c) 125°C/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

FDS6572A Rev C (W)

Typical Characteristics

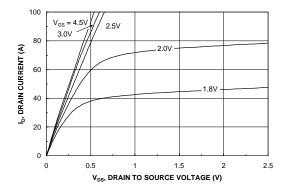


Figure 1. On-Region Characteristics.

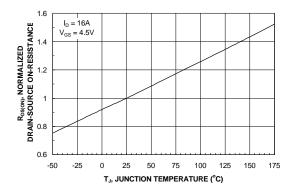


Figure 3. On-Resistance Variation with Temperature.

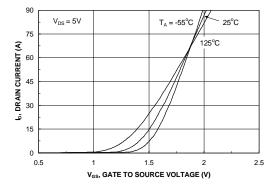


Figure 5. Transfer Characteristics.

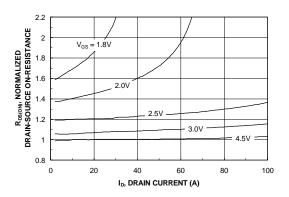


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

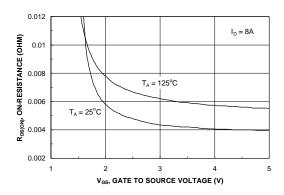


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

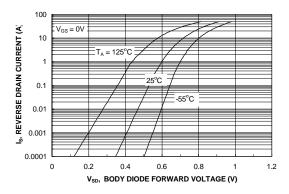
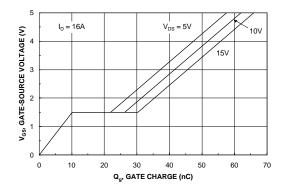


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

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Typical Characteristics



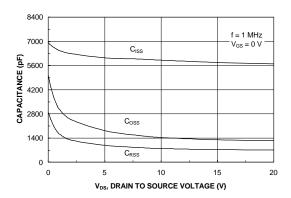


Figure 7. Gate Charge Characteristics.

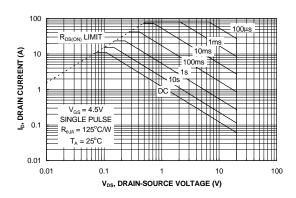


Figure 8. Capacitance Characteristics.

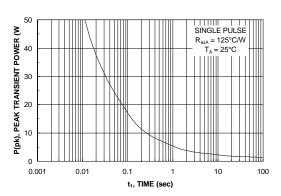


Figure 9. Maximum Safe Operating Area.



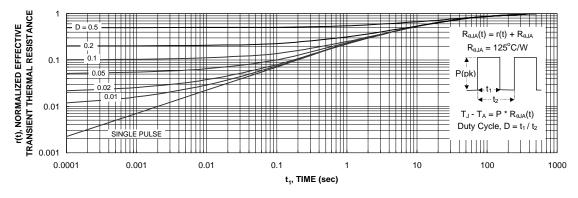


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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